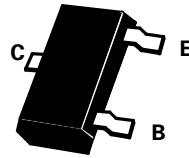


# SOT23 NPN SILICON PLANAR RF TRANSISTORS

## BFS17L BFS17H

ISSUE 4 – MARCH 2001

PARTMARKING DETAILS — BFS17L - E1L  
BFS17H - E1H



### ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	VALUE	UNIT
Collector-Base Voltage	$V_{CBO}$	25	V
Collector-Emitter Voltage	$V_{CEO}$	15	V
Emitter-Base Voltage	$V_{EBO}$	2.5	V
Peak Pulse Current	$I_{CM}$	50	mA
Continuous Collector Current	$I_C$	25	mA
Power Dissipation at $T_{amb}=25^{\circ}C$	$P_{tot}$	330	mW
Operating and Storage Temperature Range	$T_j; T_{stg}$	-55 to +150	$^{\circ}C$

### ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^{\circ}C$ ).

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS.
Collector Cut-Off Current	$I_{CBO}$			10 10	nA $\mu A$	$V_{CB}=10V, I_E=0$ $V_{CB}=10V, I_E=0,$ $T_{amb} = 100^{\circ}C$
Static Forward Current Transfer Ratio	$h_{FE}$					
BFS17L		25		100		$I_C=2.0mA, V_{CE}=1.0V$
BFS17H		70		200		$I_C=2.0mA, V_{CE}=1.0V$
		20		125		$I_C=25mA, V_{CE}=1.0V$
Transition Frequency	$f_T$		1.0 1.3		GHz GHz	$I_C=2.0mA, V_{CE}=5.0V$ $f=500MHz$ $I_C=25mA, V_{CE}=5.0V$ $f=500MHz$
Feedback Capacitance	$-C_{re}$		0.85		pF	$I_C=2.0mA, V_{CE}=5V, f=1MHz$
Output Capacitance	$C_{obo}$			1.5	pF	$V_{CB}=10V, f=1MHz$
Input Capacitance	$C_{ibo}$			2.0	pF	$V_{EB}=0.5V, f=1MHz$
Noise Figure	N		4.5		dB	$I_C=2.0mA, V_{CE}=5.0V$ $R_S=50\Omega, f=500MHz$
Intermodulation Distortion	$d_{im}$		-45		dB	$I_C=10mA, V_{CE}=6.0V$ $R_L=37.5\Omega, T_{amb}=25^{\circ}C$ $V_o=100mV$ at $f_p=183MHz$ $V_o=100mV$ at $f_q=200MHz$ measured at $f_{(2q-p)}=217MHz$

Spice parameter data is available upon request for this device

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## TYPICAL CHARACTERISTICS

